IN THE CLAIMS:

Please amend claims 1, 10, 19-29, 31-41, and 43-52 as follows:

Sub D1 C2

1. (Amended) A contact structure for electrically connecting a connecting wiring over a substrate to a wiring over another substrate by an anisotropic conductive film,

wherein said connecting wiring is a lamination film comprising a metallic film and a transparent conductive film in contact with said metallic film, and

wherein a side surface of said metallic film is covered with an insulating film along the length direction and the width direction of said lamination film.

Sub D3 C3

10. (Amended) A contact structure for electrically connecting a connecting wiring over a substrate to a wiring over another substrate by at least one grain plated with at least one of gold and chromium in an anisotropic conductive film,

wherein said connecting wiring is a lamination film comprising a metallic film and a transparent conductive film in contact with said metallic film,

wherein a side surface of said metallic film is covered with an insulating film along the length direction and the width direction of said lamination film, and

wherein said metallic film is not in contact with said grain in said anisotropic conductive film.

Sub D5 C4

19. (Amended) A semiconductor device comprising:

a circuit comprising a thin film transistor over a substrate; and

a connecting wiring over said substrate for connecting said circuit to another circuit,

wherein said connecting wiring is a lamination film comprising a metallic film and a transparent conductive film in contact with said metallic film,

wherein a side surface of said metallic film is covered with an insulating film along the length direction of said lamination film, and

wherein said lamination film has a taper shape.

20. (Amended) A semiconductor device of claim 19 wherein the protecting film is formed of the same materials as that of an insulating film between a gate wiring and a source wiring of the thin film transistor.

21. (Amended) A semiconductor device of claim 19 wherein the connecting wiring is electrically connected to a wiring of another substrate via an anisotropic conductive film.

22. (Amended) A semiconductor device of claim 19 wherein the protecting film is a resin film.

23. (Amended) A semiconductor device of claim 19 wherein a thickness of the metallic film is between 100 nm and 1 μm.

24. (Amended) A semiconductor device of claim 19 wherein the metallic film comprises a metallic layer having Al as its principal constituent, or an alloy layer containing Al.

25. (Amended) A semiconductor device of claim 19 wherein the metallic film comprises a metallic layer having W as its principal constituent, or an alloy layer containing W.

26. (Amended) A semiconductor device of claim 19 wherein the metallic film is a lamination film formed of a W layer, and an alloy layer containing W and N.

27. (Amended) A semiconductor device of claim 19 wherein a thickness of the transparent conductive film is between 50 nm and 0.5 μm.

28. (Amended) A semiconductor device of claim 19 wherein the transparent conductive film is an alloy film containing zinc oxide.

29. (Amended) A semiconductor device of claim 19 wherein the transparent conductive film is an alloy film containing zinc oxide and indium oxide.

31. (Amended) A semiconductor device comprising:

a first substrate comprising a circuit comprising a thin film transistor;

a second substrate opposing said first substrate;

a connecting wiring comprising a metallic film and a transparent conductive film in contact with said metallic film for connecting said circuit to another circuit; and

an insulating film in contact with a side surface of said metallic film,

wherein said connecting wiring and said insulating film are formed over said first substrate,

wherein said insulating film is formed along with the length direction of said lamination film, and

wherein said connecting wiring has a taper shape.

32. (Amended) A semiconductor device of claim 31 wherein the protecting film is formed of the same materials as that of an insulating film between a gate wiring and a source wiring of the thin film transistor.

33. (Amended) A semiconductor device of claim 31 wherein said connecting wiring is electrically connected to a wiring of a third substrate via an anisotropic conductive film.

34. (Amended) A semiconductor device of claim 31 wherein the protecting film is a resin film.

35. (Amended) A semiconductor device of claim 31 wherein a thickness of the metallic film is between 100 nm and 1 μm.

36. (Amended) A semiconductor device of claim 31 wherein the metallic film comprises a metallic layer having Al as its principal constituent, or an alloy layer containing Al.

37. (Amended) A semiconductor device of claim 31 wherein the metallic film comprises a metallic layer having W as its principal constituent, or an alloy layer containing W.

38. (Amended) A semiconductor device of claim 31 wherein the metallic film is a lamination film formed of a W layer, and an alloy layer containing W and N.

39. (Amended) A semiconductor device of claim 31 wherein a thickness of the transparent conductive film is between 50 nm and 0.5 μm.

40. (Amended) A semiconductor device of claim 31 wherein the transparent conductive film is an alloy film containing zinc oxide.

41. (Amended) A semiconductor device of claim 31 wherein the transparent conductive film is an alloy film containing zinc oxide and indium oxide.

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43. (Amended) A semiconductor device comprising:

a first substrate comprising a circuit comprising a thin film transistor;

a second substrate opposing said first substrate;

a connecting wiring comprising a metallic film and a transparent conductive film in contact with said metallic film for connecting said circuit to another circuit;

a column-shape spacer formed over said thin film transistor for maintaining a space between said first substrate and said second substrate; and

a protecting film in contact with a side surface of said metallic film comprising the same material as that of the column-shape spacer,

wherein said connecting wiring, said column spacer, and said protecting film are formed over said first substrate,

wherein said protecting film is formed along with the length direction of said lamination film, and

wherein said connecting wiring has a taper shape.

44. (Amended) A semiconductor device of claim 43 wherein said connecting wiring is electrically connected to a wiring of a third substrate via an anisotropic conductive film.

45. (Amended) A semiconductor device of claim 43 wherein the protecting film is a resin film.

46. (Amended) A semiconductor device of claim 43 wherein a thickness of the metallic film is between 100 nm and 1 μm.

47. (Amended) A semiconductor device of claim 43 wherein the metallic film comprises a metallic layer having Al as its principal constituent, or an alloy layer containing Al.

48. (Amended) A semiconductor device of claim 43 wherein the metallic film comprises a metallic layer having W as its principal constituent, or an alloy layer containing W.

49. (Amended) A semiconductor device of claim 43 wherein the metallic film is a lamination film formed of a W layer, and an alloy layer containing W and N.

50. (Amended) A semiconductor device of claim 43 wherein a thickness of the transparent conductive film is between 50 nm and 0.5 μm.

51. (Amended) A semiconductor device of claim 43 wherein the transparent conductive film is an alloy film containing zinc oxide.

52. (Amended) A semiconductor device of claim 43 wherein the transparent conductive film is an alloy film containing zinc oxide and indium oxide.